Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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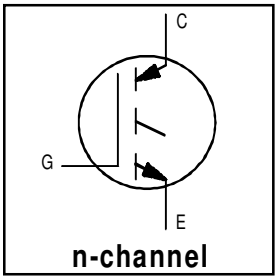
International
IOR Rectifier

PD - 91620A

IRG4BC20K-S

Short Circuit Rated
UltraFast IGBT

INSULATED GATE BIPOLAR TRANSISTOR

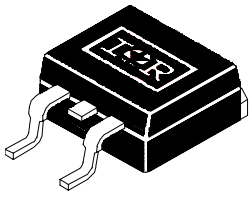


n-channel

V_{CES} = 600V

$V_{CE(on)\ typ.}$ = 2.27V

@V_{GE} = 15V, I_C = 9.0A



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Features

- High short circuit rating optimized for motor control, t_{sc} =10µs, @360V V_{CE} (start), T_J = 125°C, V_{GE} = 15V
- Combines low conduction losses with high switching speed
- Latest generation design provides tighter parameter distribution and higher efficiency than previous generations

Benefits

- As a Freewheeling Diode we recommend our HEXFRED™ ultrafast, ultrasoft recovery diodes for minimum EMI / Noise and switching losses in the Diode and IGBT
- Latest generation 4 IGBTs offer highest power density motor controls possible
- This part replaces the IRGBC20K-S and IRGBC20M-S devices

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
I_C @ T_C = 25°C	Continuous Collector Current	16	A
I_C @ T_C = 100°C	Continuous Collector Current	9.0	
I_{CM}	Pulsed Collector Current ①	32	
I_{LM}	Clamped Inductive Load Current ②	32	
t_{sc}	Short Circuit Withstand Time	10	µs
V_{GE}	Gate-to-Emitter Voltage	±20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	29	mJ
P_D @ T_C = 25°C	Maximum Power Dissipation	60	W
P_D @ T_C = 100°C	Maximum Power Dissipation	24	
T_J	Operating Junction and	-55 to +150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	2.1	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.5	—	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted,steady-state)⑥	—	40	
Wt	Weight	1.44	—	g

4/24/2000

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V_{GE} = 0V, I_C = 250µA
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	V_{GE} = 0V, I_C = 1.0A
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.49	—	V/°C	V_{GE} = 0V, I_C = 1.0mA
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	2.00	—	V	I_C = 6.0A
		—	2.27	2.8		I_C = 9.0A V_{GE} = 15V
		—	3.01	—		I_C = 16A See Fig.2, 5
		—	2.43	—		I_C = 9.0A , T_J = 150°C
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		V_{CE} = V_{GE}, I_C = 250µA
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-10	—	mV/°C	V_{CE} = V_{GE}, I_C = 250µA
g_{fe}	Forward Transconductance ⑤	2.9	4.3	—	S	V_{CE} = 100 V, I_C = 9.0A
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	µA	V_{GE} = 0V, V_{CE} = 600V
		—	—	2.0		V_{GE} = 0V, V_{CE} = 10V, T_J = 25°C
		—	—	1000		V_{GE} = 0V, V_{CE} = 600V, T_J = 150°C
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	34	51	nC	I_C = 9.0A
Q_{ge}	Gate - Emitter Charge (turn-on)	—	4.9	7.4		V_{CC} = 400V See Fig.8
Q_{gc}	Gate - Collector Charge (turn-on)	—	14	21		V_{GE} = 15V
$t_{d(on)}$	Turn-On Delay Time	—	28	—	ns	T_J = 25°C
t_r	Rise Time	—	27	—		I_C = 9.0A, V_{CC} = 480V
$t_{d(off)}$	Turn-Off Delay Time	—	150	220		V_{GE} = 15V, R_G = 50Ω
t_f	Fall Time	—	100	150		Energy losses include "tail"
E_{on}	Turn-On Switching Loss	—	0.15	—	mJ	See Fig. 9,10,14
E_{off}	Turn-Off Switching Loss	—	0.25	—		
E_{ts}	Total Switching Loss	—	0.40	0.6		
t_{sc}	Short Circuit Withstand Time	10	—	—	µs	V_{CC} = 400V, T_J = 125°C V_{GE} = 15V, R_G = 50Ω , V_{CPK} < 500V
$t_{d(on)}$	Turn-On Delay Time	—	28	—	ns	T_J = 150°C,
t_r	Rise Time	—	29	—		I_C = 9.0A, V_{CC} = 480V
$t_{d(off)}$	Turn-Off Delay Time	—	190	—		V_{GE} = 15V, R_G = 50Ω
t_f	Fall Time	—	190	—		Energy losses include "tail"
E_{ts}	Total Switching Loss	—	0.68	—	mJ	See Fig. 11,14
E_{on}	Turn-On Switching Loss	—	0.07	—	mJ	T_J = 25°C, V_{GE} = 15V, R_G = 50Ω
E_{off}	Turn-Off Switching Loss	—	0.13	—		I_C = 6.0A, V_{CC} = 480V
E_{ts}	Total Switching Loss	—	0.20	—		Energy losses include "tail"
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	450	—	pF	V_{GE} = 0V
C_{oes}	Output Capacitance	—	61	—		V_{CC} = 30V See Fig. 7
C_{res}	Reverse Transfer Capacitance	—	14	—		f = 1.0MHz

Details of note ① through ⑥ are on the last page

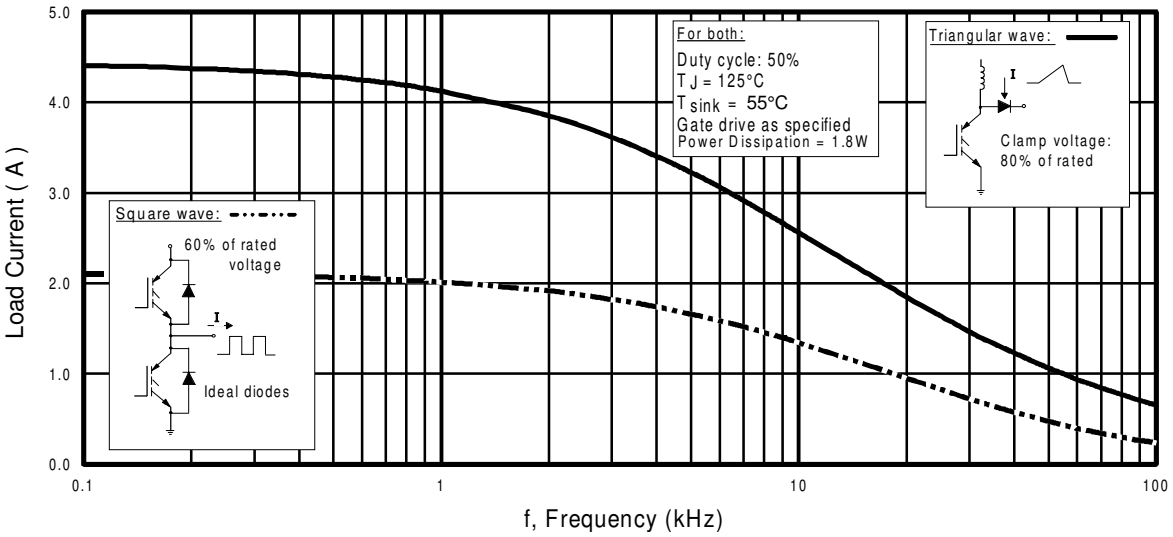


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

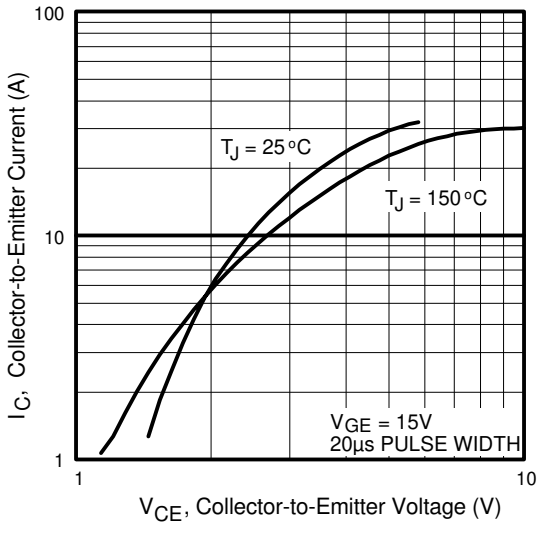


Fig. 2 - Typical Output Characteristics

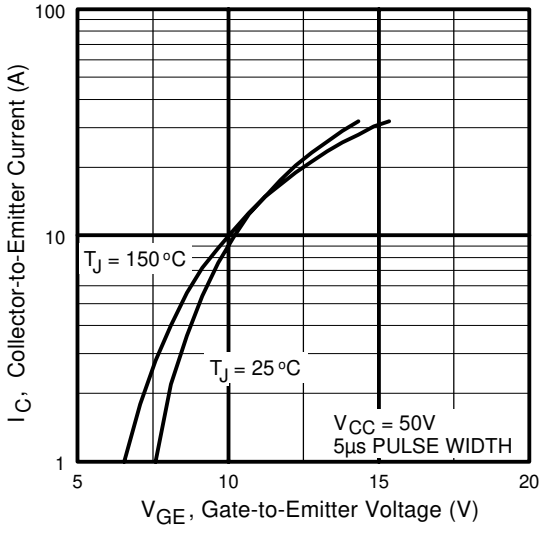


Fig. 3 - Typical Transfer Characteristics

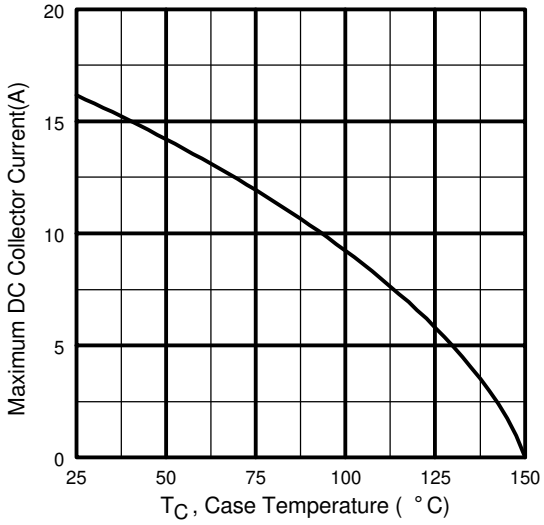


Fig. 4 - Maximum Collector Current vs. Case Temperature

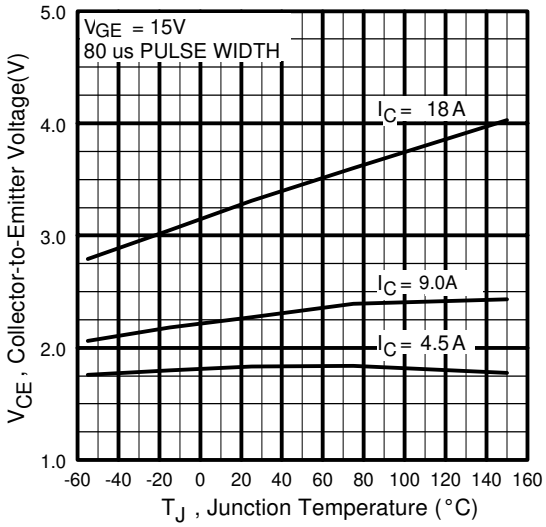


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

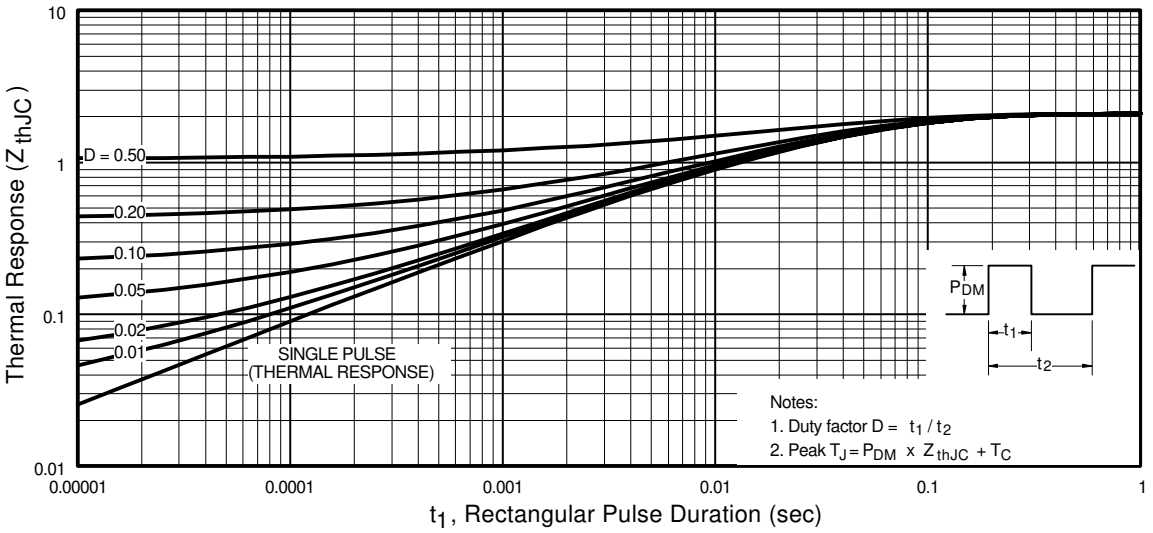


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

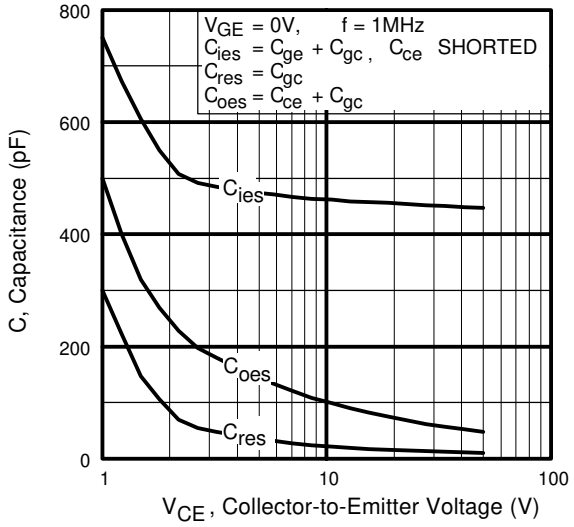


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

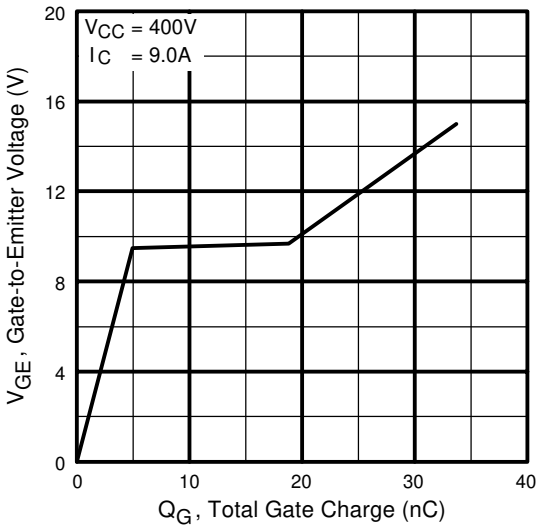


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

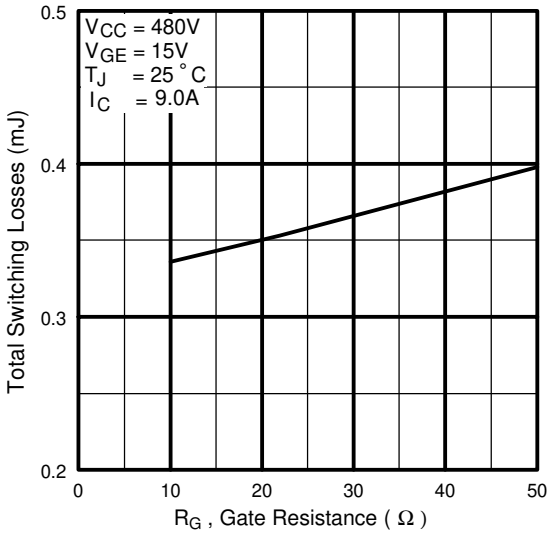


Fig. 9 - Typical Switching Losses vs. Gate Resistance

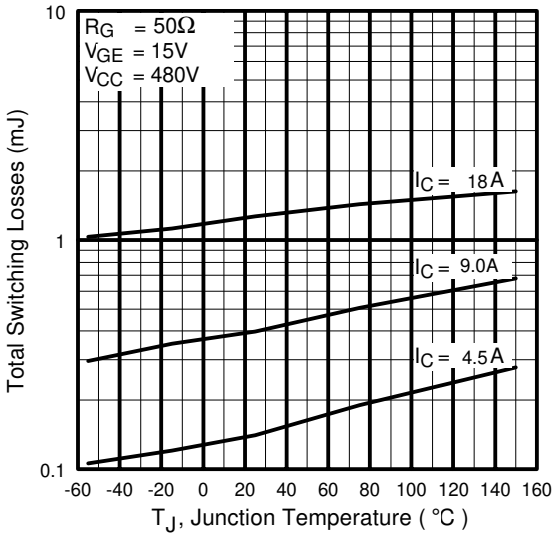


Fig. 10 - Typical Switching Losses vs. Junction Temperature

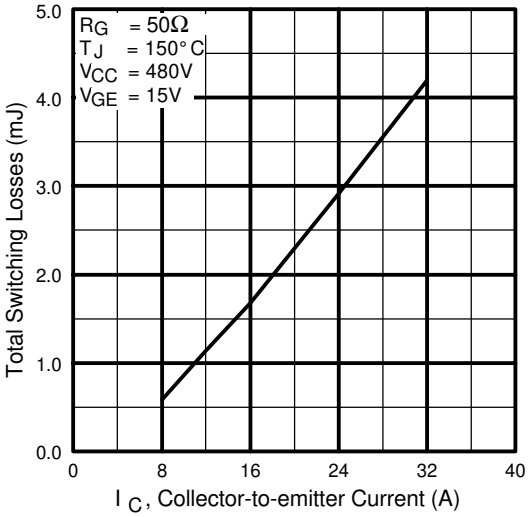


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

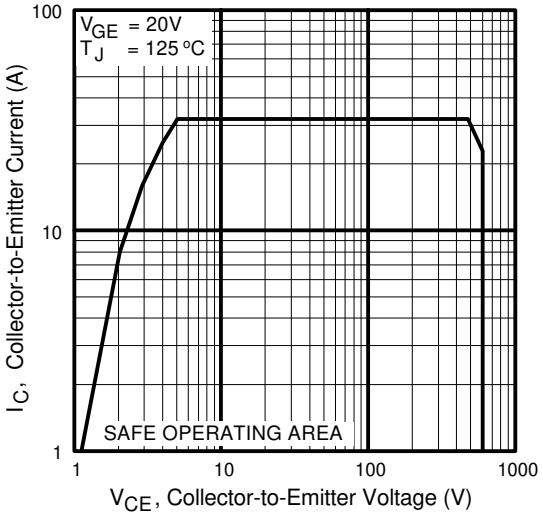
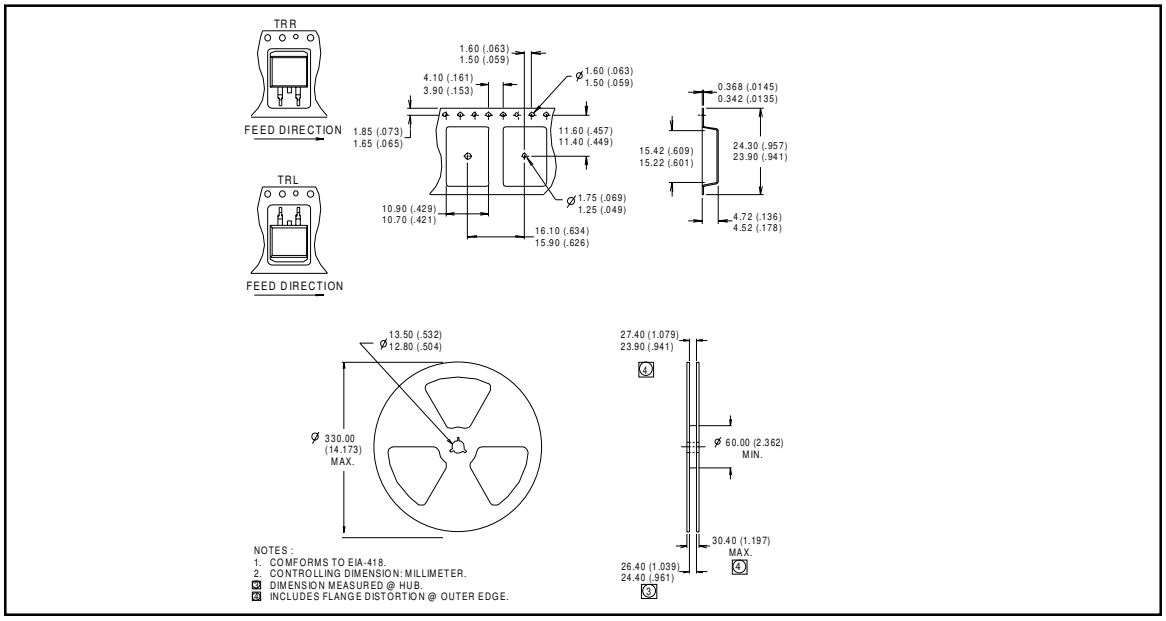


Fig. 12 - Turn-Off SOA

Tape & Reel Information

D²Pak



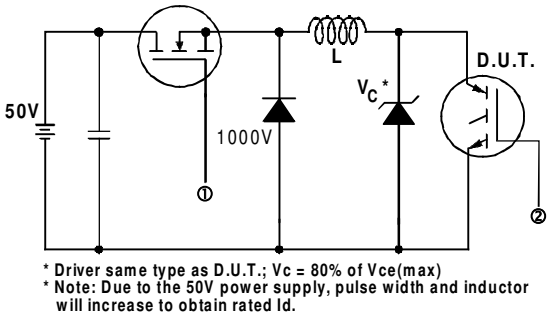


Fig. 13a - Clamped Inductive Load Test Circuit

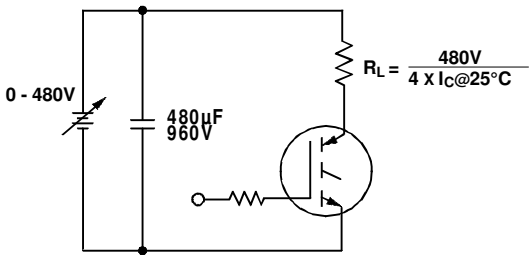


Fig. 13b - Pulsed Collector Current Test Circuit

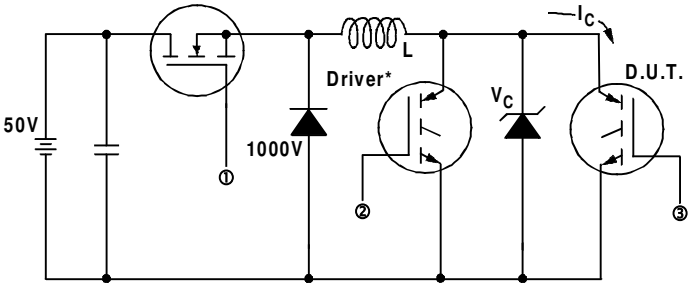


Fig. 14a - Switching Loss Test Circuit

*** Driver same type as D.U.T., VC = 480V**

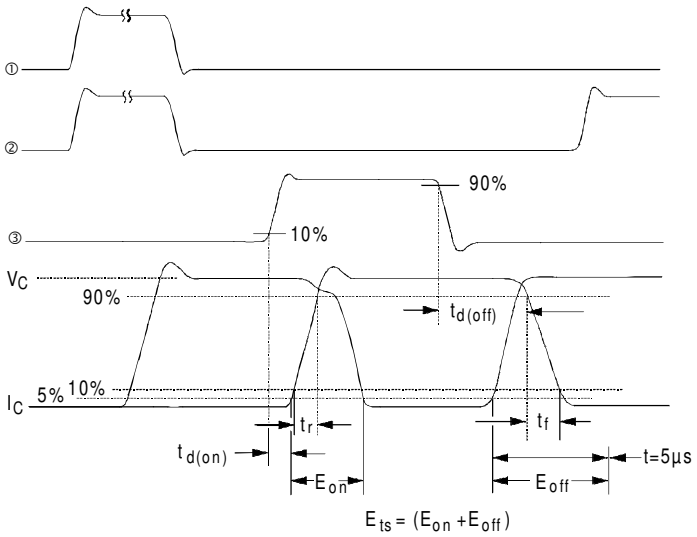


Fig. 14b - Switching Loss Waveforms

Notes:

① Repetitive rating; V_{GE} = 20V, pulse width limited by max. junction temperature. (See fig. 13b)

② V_{CC} = 80%(V_{CES}), V_{GE} = 20V, L = 10µH, R_G = 50Ω, (See fig. 13a)

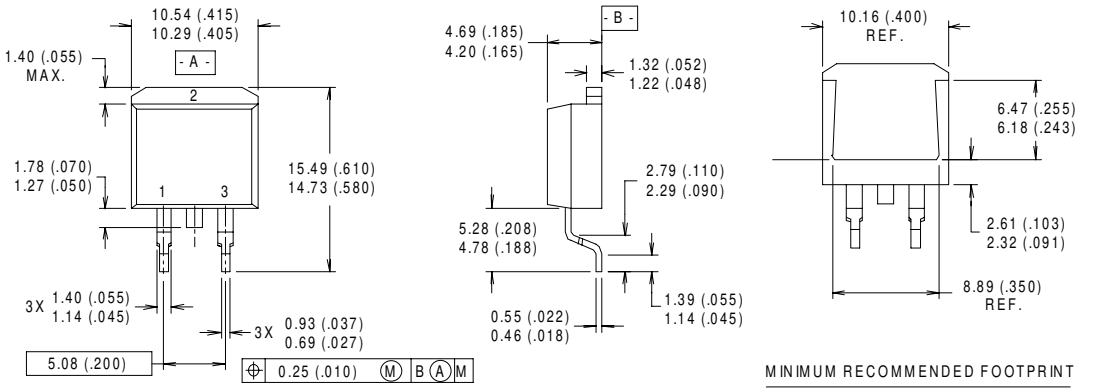
③ Repetitive rating; pulse width limited by maximum junction temperature.

④ Pulse width ≤ 80µs; duty factor ≤ 0.1%.

⑤ Pulse width 5.0µs, single shot.

⑥ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

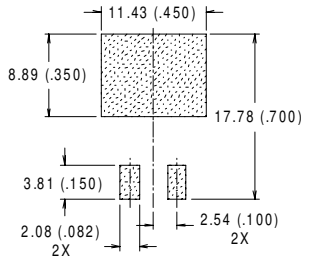
D²Pak Package Outline



NOTES:
1 DIMENSIONS AFTER SOLDER DIP.
2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
3 CONTROLLING DIMENSION : INCH.
4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

LEAD ASSIGNMENTS
1 - GATE
2 - DRAIN
3 - SOURCE

MINIMUM RECOMMENDED FOOTPRINT



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IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
IR EUROPEAN REGIONAL CENTRE: 439/445 Godstone Rd, Whyteleafe, Surrey CR3 OBL, UK Tel: ++ 44 (0)20 8645 8000
IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200
IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 (0) 6172 96590
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IR TAIWAN:16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673 Tel: 886-(0)2 2377 9936
Data and specifications subject to change without notice. 10/00

Note: For the most current drawings please refer to the IR website at:
http://www.irf.com/package/